This listing of claims replaces all prior versions, and listings, of claims in the application:

In the Claims:

1-25. (Cancelled)

26. (Currently Amended) A method of fabricating a nitride semiconductor device, comprising ~~the steps of~~:

~~adjusting to within a range from 80 to 160 μm a thickness of~~ forming a nitride semiconductor wafer ~~formed~~ by depositing on a substrate that exhibits cleavage a nitride semiconductor layer ~~formed out of~~ comprising a compound containing a group III element and nitrogen and ~~including,~~ having a cleavage plane crystallographically similar [[equal]] to a cleavage plane of the substrate[[, with]] and comprising a plurality of stripe-shaped optical waveguides formed at an equal ~~intervals~~ separation in the nitride semiconductor layer;

adjusting a thickness of the nitride semiconductor wafer so that the thickness falls within a range from 80 to 160 μm;

forming a plurality of cleavage guide grooves in a shape of discontinuous broken lines in a top surface of the nitride semiconductor wafer by scribing from above the nitride semiconductor layer ~~in such a way~~ so that the cleavage guide grooves reach the substrate and no cleavage guide groove extends over the stripe-shaped optical wave guides; and

cleaving the nitride semiconductor wafer along the cleavage guide grooves~~,~~

~~wherein the cleavage guide grooves are formed elsewhere than right above the stripe-shaped optical waveguides~~.

27. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 26, wherein the substrate [[is]] comprises a nitride semiconductor

substrate ~~formed out of~~ comprising [[a]] another compound containing a group III element and nitrogen.

28. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 26, wherein a ~~depth *d*~~ distance from the top surface of the nitride semiconductor wafer to bottoms of the cleavage guide grooves is ~~within a range $1 \leq d \leq$~~ equal to or larger than 1 μm and equal to or smaller than 10 μm.

29. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 28, wherein the forming of the cleavage guide grooves [[are]] is such that the cleavage guide grooves are discontinuous in a same broken line with an equal interval ~~formed with intervals~~ of 1 mm or shorter ~~left between every two adjacent ones thereof on a same broken line~~.

30-37. (Cancelled)

38. [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 26, ~~wherein, when a semiconductor layer of a material that cleaves in a different direction from the nitride semiconductor is formed at an interface between the nitride semiconductor layer and the substrate,~~ further comprising forming [[first]] a plurality of cleavage assist grooves ~~are formed~~ in a shape of discontinuous broken lines in [[a]] the top surface of the nitride semiconductor [[layer]] wafer so as to ~~a depth reaching~~ reach half a thickness of the nitride semiconductor layer by scribing from above the top surface of the nitride semiconductor layer, ~~and then~~ wherein the cleavage guide grooves are formed by scribing from bottom surfaces of the cleavage assist grooves.

39. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 38, wherein a ~~depth *d*~~ distance from the top surface of the nitride

semiconductor wafer to a deepest end of the cleavage guide grooves is ~~within a range $1 \leq d \leq$~~ equal to or larger than 1 μm and equal to or smaller than 10 μm.

40. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 39, wherein the forming of the cleavage guide grooves [[are]] is such that the cleavage guide grooves are discontinuous in a same broken line with an equal interval ~~formed with intervals~~ of 1 mm or shorter ~~left between every two adjacent ones thereof on a same broken line~~.

41-48. (Cancelled)

49. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 26, further comprising ~~the step of: before the step of cleaving the nitride semiconductor wafer,~~ forming cleavage assist grooves in a bottom surface of the nitride semiconductor wafer by scribing from below the nitride semiconductor substrate~~, wherein the cleavage guide grooves and the cleavage assist grooves are~~ so ~~formed~~ that the cleavage guide grooves are located along center axes of the cleavage assist grooves, prior to the cleaving of the nitride semiconductor wafer.

50. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 49, wherein the substrate [[is]] comprises a nitride semiconductor substrate ~~formed out of~~ comprising [[a]] another compound containing a group III element and nitrogen.

51. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 49, wherein a ~~depth d~~ distance from the top surface of the nitride semiconductor wafer to a deepest end of the cleavage guide grooves is ~~within a range $1 \leq d \leq$~~ equal to or larger than 1 μm and equal to or smaller than 10 μm.

52. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 51, wherein the forming of the cleavage guide grooves [[are]] is such that the cleavage guide grooves are discontinuous in a same broken line with an equal interval ~~formed with intervals~~ of 1 mm or shorter ~~left between every two adjacent ones thereof on a same broken line~~.

53-60. (Cancelled)

61. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 49, ~~wherein, when a semiconductor layer of a material that cleaves in a different direction from the nitride semiconductor is formed at an interface between the nitride semiconductor layer and the substrate,~~ further comprising forming [[first]] a plurality of cleavage assist grooves ~~are formed~~ in a shape of discontinuous broken lines in [[a]] the top surface of the nitride semiconductor [[layer]] wafer so as to ~~a depth reaching~~ reach half a thickness of the nitride semiconductor layer by scribing from above the top surface of the nitride semiconductor layer, ~~and then~~ wherein the cleavage guide grooves are formed by scribing from bottom surfaces of the cleavage assist grooves.

62. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 61, wherein a ~~depth *d*~~ distance from the top surface of the nitride semiconductor wafer to a deepest end of the cleavage guide grooves is ~~within a range $1 \leq d \leq$~~ equal to or larger than 1 μm and equal to or smaller than 10 μm.

63. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 62, wherein the forming of the cleavage guide grooves [[are]] is such that the cleavage guide grooves are discontinuous in a same broken line with an equal

interval ~~formed with intervals~~ of 1 mm or shorter ~~left between every two adjacent ones thereof on a same broken line~~.

64-71. (Cancelled)

72. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 26, wherein the forming of the cleavage guide grooves [[are]] is such that the cleavage guide grooves are discontinuous in a same broken line with an equal interval ~~formed with intervals~~ of 1 mm or shorter ~~left between every two adjacent ones thereof on a same broken line~~.

73. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 26, wherein ~~the~~ at least one cleavage guide ~~grooves are~~ groove is formed ~~in every interval~~ between [[the]] any two neighboring stripe-shaped optical waveguides [[on]] along a same broken line of the cleavage guide grooves.

74-75. (Cancelled)

76. (Currently Amended) A method of fabricating a nitride semiconductor device, comprising ~~the steps of~~:

~~adjusting to within a range from 80 to 160 μm a thickness of~~ forming a nitride semiconductor wafer ~~formed~~ by depositing on a substrate that exhibits cleavage a nitride semiconductor layer ~~formed out of~~ comprising a compound containing a group III element and nitrogen and ~~including,~~ having a cleavage plane crystallographically similar [[equal]] to a cleavage plane of the substrate[[, with]] and comprising a plurality of stripe-shaped optical waveguides formed at an equal ~~intervals~~ separation in the nitride semiconductor layer;

adjusting a thickness of the nitride semiconductor wafer so that the thickness falls within a range from 80 to 160 μm;

forming a plurality of cleavage guide grooves in a shape of discontinuous broken lines in a bottom surface of the nitride semiconductor wafer by scribing from below the substrate so that no cleavage guide groove extends under the stripe-shaped optical wave guides; and

cleaving the nitride semiconductor wafer along the cleavage guide grooves~~,~~

~~wherein the cleavage guide grooves are formed elsewhere than right below the stripe-shaped optical waveguides~~.

77. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 76, wherein the substrate [[is]] comprises a nitride semiconductor substrate ~~formed out of~~ comprising [[a]] another compound containing a group III element and nitrogen.

78-82. (Cancelled)

83. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 76, wherein the forming of the cleavage guide grooves [[are]] is such that the cleavage guide grooves are discontinuous in a same broken line with an equal interval ~~formed with intervals~~ of 1 mm or shorter ~~left between every two adjacent ones thereof on a same broken line~~.

84-86. (Cancelled)